

## **FJP3835**

### **Power Amplifier**

- High Current Capability: I<sub>C</sub>=8A
  High Power Dissipation
  Wide S.O.A



1.Base 2.Collector 3.Emitter

## **NPN Epitaxial Silicon Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	200	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
I <sub>C</sub>	Collector Current (DC)	8	Α
I <sub>CP</sub>	Collector Current (Pulse)	16	Α
PC	Collector Dissipation (T <sub>C</sub> =25°C)	50	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

## Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C=5mA$ , $I_E=0$	200			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, R <sub>BE</sub> =∞	120			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E=5mA$ , $I_C=0$	8			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =80V, $I_{E}$ =0			0.1	mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =4V, $I_{C}$ =0			0.1	mA
h <sub>FE</sub>	* DC Current Gain	$V_{CE}$ =4V, $I_{C}$ =3A	120		250	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =3A, I <sub>B</sub> =0.3A			0.5	V
V <sub>BE</sub> (sat)	Base-Emitter On Voltage	I <sub>C</sub> =3A, I <sub>B</sub> =0.3A			1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =5V, I <sub>C</sub> =1A		30		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, f=1MHz		210		pF
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> =20V,		0.26		μs
t <sub>F</sub>	Fall Time	I <sub>C</sub> =1A=10I <sub>B1</sub> =-10I <sub>B2</sub>		0.68		μs
t <sub>STG</sub>	Storage Time	$R_L=20\Omega$		6.68		μs

<sup>\*</sup> Pulse Test : PW=20µs

# **Typical Characteristics**

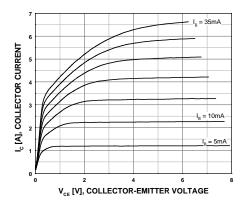


Figure 1. Static Characterstic

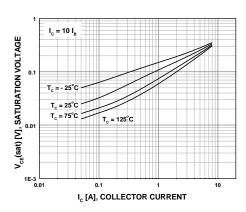


Figure 3. Collector-Emitter Saturation Voltage

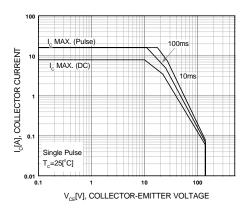


Figure 5. Safe Operating Area

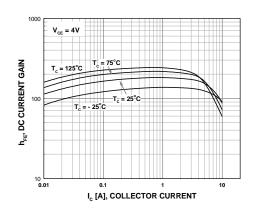


Figure 2. DC current Gain

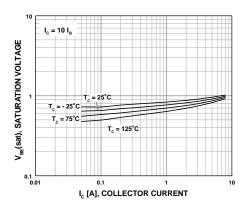


Figure 4. Base-Emitter Saturation Voltage

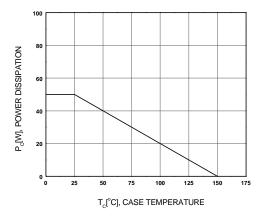
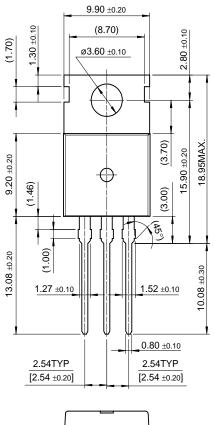
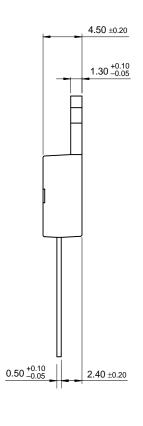


Figure 6. Power Derating

# **Package Demensions**

# TO-220





10.00 ±0.20

Dimensions in Millimeters

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